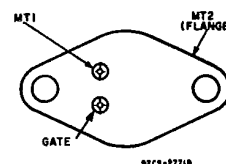


File Number **300****T4700 Series****15-Ampere Silicon Triacs**

For Phase-Control and Load-Switching Applications

Features:

- 800V, 125 Deg. C T_J Operating
- High dv/dt and di/dt Capability
- Low Switching Losses
- High Pulse Current Capability
- Low Forward and Reverse Leakage
- Sipos Oxide Glass Multilayer Passivation System
- Advanced Unisurface Construction
- Precise Ion Implanted Diffusion Source

TERMINAL DESIGNATIONS

JEDEC TO-213AA

The RCA T4700 Series are gate-controlled full-wave ac silicon switches. They are designed to switch from an off-state to a conducting state for either polarity of applied voltage with positive or negative gate triggering.

These devices are intended for the control of ac loads in applications such as space heater, oven and furnace controls, motor controls, and lamp loads.

MAXIMUM RATINGS, Absolute-Maximum Values:

		T4700B	T4700D	T4700M	T4700N	
REPETITIVE PEAK OFF-STATE VOLTAGE:■						
Gate Open	V_{DROM}	200	400	600	800	V
RMS ON-STATE CURRENT:						
$T_C = 95^\circ\text{C}$, conduction angle = 360°	$I_{T(RMS)}$		15			A
PEAK SURGE (NON-REPETITIVE) ON-STATE CURRENT:	I_{TSM}					
For one full cycle of applied principal voltage			100			A
60 Hz (sinusoidal)			85			A
For one full cycle of applied principal voltage			See Fig. 3			
(50-Hz, sinusoidal)						
For more than one full cycle of applied voltage						
PEAK GATE-TRIGGER CURRENT:						
For 1 μs max.	I_{GTM}		4			A
FUSING CURRENT (for triac protection):						
$T_J = -40$ to 100°C , $t = 1.25$ to 10 ms	I^2t		50			A ² s
GATE POWER DISSIPATION:						
Peak* (for 1 μs max. and $I_{GTM} \leq 4$ A)	P_{GM}		16			W
Average (averaging time = 10 ms max.)	$P_{G(AV)}$		0.45			W
TEMPERATURE RANGE:Δ						
Storage	T_{stg}		-40 to 150			$^\circ\text{C}$
Operating (Case)	T_C		-40 to 125			$^\circ\text{C}$
PIN TEMPERATURE (During soldering):						
At distances $\geq 1/32$ in. (0.8 mm) from seating plane for 10 s max.	T_P		225			$^\circ\text{C}$

■ For either polarity of main terminal 2 voltage (V_{MT2}) with reference to main terminal 1.

* For either polarity of gate voltage (V_G) with reference to main terminal 1.

Δ For temperature measurement reference point, see *Dimensional Outline*.

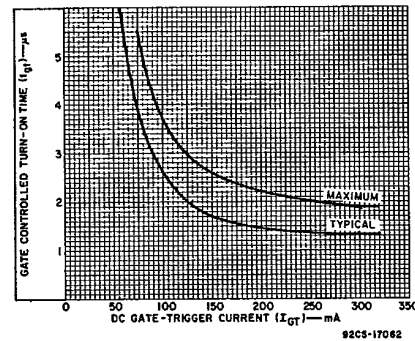
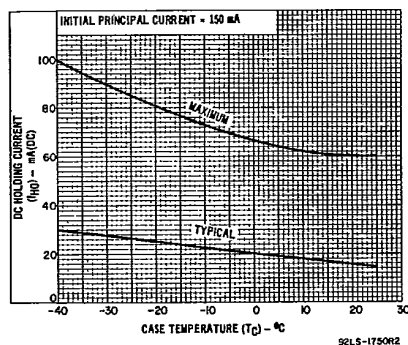
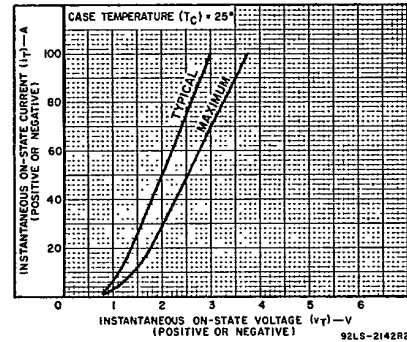
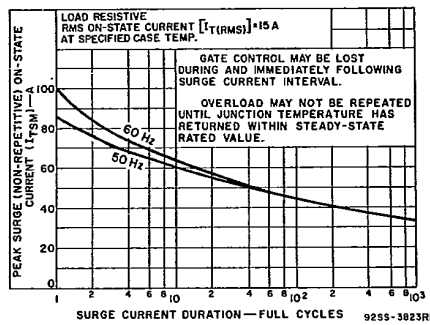
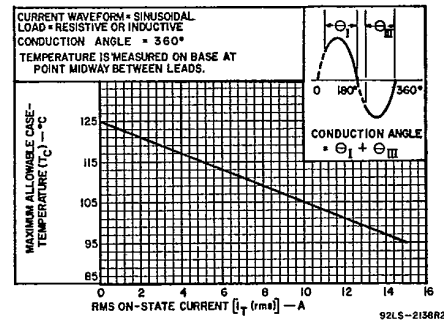
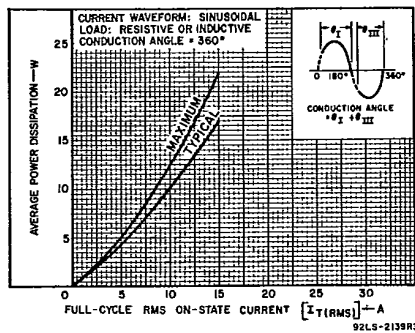
Trlacs

T4700 Series**ELECTRICAL CHARACTERISTICS**At Maximum Ratings and at Indicated Case Temperature (T_C) Unless Otherwise Specified

CHARACTERISTIC	SYMBOL	LIMITS			UNITS
		For All Types Unless Otherwise Specified			
		Min.	Typ.	Max.	
Peak Off-State Current [♦] Gate open, $T_J = 125^\circ\text{C}$, $V_{DROM} = \text{Max. rated value}$	I_{DROM}	—	0.2	4	mA
Instantaneous On-State Voltage [♦] For $I_T = 30\text{A}$ (peak), $T_C 25^\circ\text{C}$	V_T	—	1.6	2.0	V
DC Holding Current [♦] Gate open, Initial principal current = 150 mA (DC), $v_D = 12\text{V}$: $T_C = 25^\circ\text{C}$	I_{HO}	—	15	60	mA
For other case temperatures			See Fig. 5		
Critical Rate of Applied Commutating Voltage [♦] For $v_D = V_{DROM}$, $I_{T(RMS)} = 15\text{A}$, commutating $di/dt = 8\text{A/ms}$, and gate unenergized At $T_C = +95^\circ\text{C}$	dv/dt	2	10	—	V/ μs
Critical Rate of Rise of Off-State Voltage [♦] For $v_D = V_{DROM}$, exponential voltage rise, and gate open At $T_C = 125^\circ\text{C}$ T4700B	dv/dt	30	150	—	V/ μs
T4700D		20	100	—	
T4700M		15	75	—	
T4700N		10	50	—	
DC Gate-Trigger Current [♦] ■ For $v_D = 6\text{ volts (dc)}$, $R_L = 12\text{ ohms}$, $T_C = +25^\circ$, and Specified Triggering Mode: I ⁺ Mode: V_{T2} is positive, V_G is positive	I_{GT}	—	15	30	mA
I ⁻ Mode: V_{T2} is positive, V_G is negative		—	35	80	
III ⁺ Mode: V_{T2} is negative, V_G is positive		—	35	80	
III ⁻ Mode: V_{T2} is negative, V_G is negative		—	15	30	
For other case temperatures			See Figs. 7 & 9		
DC Gate-Trigger Voltage [♦] ■ For $v_D = 6\text{ volts (dc)}$ and $R_L = 12\text{ ohms}$ At $T_C = +25^\circ$	V_{GT}	—	1	2.5	V
For other case temperatures		0.2	See Fig. 11	—	
For $v_D = V_{DROM}$, $R_L = 125\ \Omega$, $T_C = 125^\circ\text{C}$					
Gate-Controlled Turn-On Time (Delay Time + Rise Time) For $v_D = V_{DROM}$, $I_G = 160\text{ mA}$, $t_r = 0.1\ \mu\text{s}$, $I_T = 25\text{ A}$ (peak), $T_C = 25^\circ\text{C}$	t_{gt}	—	1.6	2.5	μs
Thermal Resistance: Junction-to-Case	$R_{\theta JC}$	—	—	1.3	$^\circ\text{C/W}$

[♦]For either polarity of main terminal 2 voltage (V_{T2}) with reference to main terminal 1.■For either polarity of gate voltage (V_G) with reference to main terminal 1.

T4700 Series



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DT-25-15

Triacs

T4700 Series

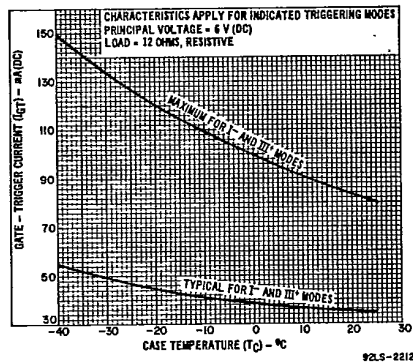


Fig. 7 — DC gate-trigger current characteristics for I- and III+ modes.

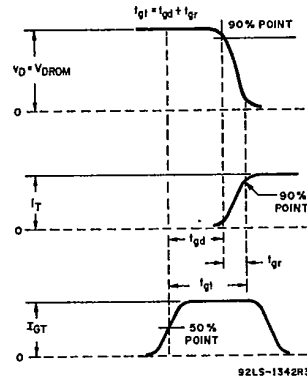
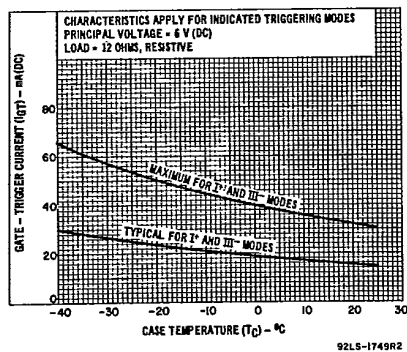
Fig. 8 — Waveshapes of t_{gt} characteristics test.

Fig. 9 — DC gate-trigger current characteristics for I+ and III- modes.

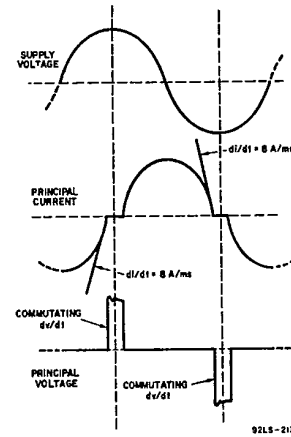
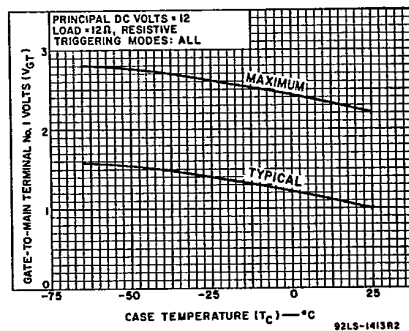
Fig. 10 — Waveshapes of commutating dv/dt characteristics.

Fig. 11 — DC gate-trigger voltage characteristics.